Abstracts

Intrinsic Response Time of Normally Off MESFET's of GaAs, Si, and InP

M. Ino and M. Ohmori. "Intrinsic Response Time of Normally Off MESFET's of GaAs, Si, and InP." 1980 Transactions on Microwave Theory and Techniques 28.5 (May 1980 [T-MTT] (Special Issue on Gigabit Logic for Microwave Systems)): 456-459.

A response time of normally off MESFET's for high-speed logic circuits made of GaAs, Si, and InP was calculated using a two-dimensional numerical analysis. The results indicate that GaAs is the best material among them. The step response of the InP FET is not as fast as expected from v/E characteristics due to low electric field in the channel for low-power logic operation of a normally off FET.

❑ Return to main document.

Click on title for a complete paper.